

IN THE SPECIFICATION

Please add the following paragraph after the TITLE and before the “TECHNICAL FIELD” section starting on page 1, of the specification.

This is a U.S. national stage of application No. PCT/JP2004/003631, filed on 18 March 2004. Priority under 35 U.S.C. §119(a) and 35 U.S.C. §365(b) is claimed from Japanese Application No. 2003-79290, filed 24 March 2003, the disclosure of which is also incorporated herein by reference.

Please replace the paragraph on page 4, beginning on line 11, with the following:

Embodiments of the present invention are described with respect to drawings. First, Fig. 1 is a view schematically showing a configuration of a MIS transistor 1 as a semiconductor device of the present invention. In this figure, reference numeral 2 denotes a Si monocrystal substrate (hereinafter simply referred to as a Si substrate), and the resistivity thereof is from 0.01 to 15 Ω ·cm, for example. Reference numeral 3 denotes an element isolation oxide film for isolating elements, which is formed by thermal oxidation of the Si ~~substrate 1~~substrate 2. Reference numeral 4 denotes a gate insulating film, which is composed of an interface layer 5, a diffusion suppressing layer 6 and a high-k film 7. A method for forming the gate insulating film 4 is specifically described later.